

# 1Mbit/s High Speed Phototransistor Optocoupler

#### **Features**

- High speed 1MBit/s
- High isolation voltage between input and output (Viso=5000 Vrms)
- Guaranteed CTR performance from 0°C to 70°C
- Operating emperature range -55°C to 100°C
- MSL class 1
- Regulatory Approvals
  - ✓ UL UL1577 (E364000)
  - ✓ VDE EN60747-5-5(VDE0884-5)
  - ✓ CQC GB4943.1, GB8898(14001104779)
  - ✓ IEC62368 (FI/41119)

# **Description**

The 6N135, 6N136, CT4502 and CT4503 devices each consist of an infrared emitting diode, optically coupled to a high speed photo detector transistor.

A separate connection for the photodiode bias and output-transistor collector increase the speed by several orders of magnitude over conventional phototransistor couplers by reducing the base-collector capacitance of the input transistor.

The devices are packaged in an 8-pin DIP package and also available in gullwing (400mil) and surface mount lead forming.

# **Applications**

- Line receivers
- Telecommunication equipment
- High speed logic ground isolation
- Feedback loop in switch-mode power supplies
- Home appliances

# Package Outline

# Anode 2 7 VB Cathode 3 6 Collector 5 Emitter

**Schematic** 

Pin 7 not connected for CT4502/CT4503

Page 1

Note: Different bending options available. See package dimension.



# 1Mbit/s High Speed Phototransistor Optocoupler

## Absolute Maximum Ratings $T_A = 25$ °C, unless otherwise specified

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage (AC, 1 minute, 40 ~ 60% R.H.)	5000	V <sub>RMS</sub>	
Topr	Operating temperature	-55 ~ +100	°C	
Тѕтс	Storage temperature	-55 ~ +125	°C	
TsoL	Soldering temperature (For 10 seconds)	260	°C	
Emitter				
l <sub>F</sub>	Forward current	25	mA	
I <sub>FP</sub>	Peak forward current (50% duty, 1ms P.W)	50	mA	
I <sub>F(TRANS)</sub>	Peak transient current (≤1µs P.W,300pps)	1	А	
V <sub>R</sub>	Reverse voltage	5	V	
P <sub>D</sub>	Power dissipation	40	mW	
Detector				
PD	Power dissipation	100	mW	
V <sub>EBR</sub>	Emitter-Base reverse voltage	5	V	
lв	Base current	5	mA	
I <sub>O(AVG)</sub>	Average Output current	8	mA	
I <sub>O</sub> (Peak)	Peak Output current	16	mA	
Vo	Output voltage	-0.5 to 20	V	
Vcc	Supply voltage	-0.5 to 30	V	



**Electrical Characteristics**  $T_A = 0 - 70^{\circ}C$  (unless otherwise specified). Typical values are measured at  $T_A = 25^{\circ}C$  and  $V_{CC} = 5V$ 

#### **Emitter Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	IF = 16mA	-	1.45	1.6	V	
VR	Reverse Voltage	IR = 10μA	5.0	-	-	V	
$\Delta V_F/\Delta T_A$	Temperature coefficient of forward voltage	IF =16mA	-	-1.8	-	mV/°C	

#### **Detector Characteristics**

Symbol	Parameters	Test Conditions	Min	Тур	Мах	Units	Notes
	Logic High Output Current	I <sub>F</sub> =0mA, V <sub>O</sub> =V <sub>CC</sub> =5.5V,	-	0.001	0.5		
		T <sub>A</sub> =25°C					
Іон		I <sub>F</sub> =0mA, V <sub>O</sub> =V <sub>CC</sub> =15V,		0.01	1	μA	
		T <sub>A</sub> =25°C	-				
		I <sub>F</sub> =0mA, V <sub>O</sub> =V <sub>CC</sub> =15V	-	-	50		
Iccl	Lacia Laur Cumply Cumpat	I <sub>F</sub> =16mA, V <sub>O</sub> =Open,		140	200	μА	
ICCL	Logic Low Supply Current	Vcc=15V	-				
	Logic High Supply Current	I <sub>F</sub> =0mA, V <sub>O</sub> =Open, V <sub>CC</sub> =15V,		0.01	1		
Іссн		T <sub>A</sub> =25°C	-		•	μA	
ICCH		IF=0mA, VO=Open,	_			μΑ	
		VCC=15V	_	_	2		



**Electrical Characteristics**  $T_A = 0 - 70^{\circ}\text{C}$  (unless otherwise specified). Typical values are measured at  $T_A = 25^{\circ}\text{C}$  and  $V_{CC} = 5V$ 

#### **Transfer Characteristics**

Symbol	Parameters		Test Conditions	Min	Тур	Мах	Units	Notes
		6N135		7	-	50		
		6N136	I <sub>F</sub> =16mA, V <sub>O</sub> =0.4V,V <sub>CC</sub> =4.5V,					
		CT4502	T <sub>A</sub> =25°C	19	-	50		
CTR	Current Transfer	CT4503					%	
CIK	Ratio	6N135		5	-	-	/0	
		6N136	I <sub>F</sub> =16mA, V <sub>O</sub> =0.5V, V <sub>CC</sub> =4.5V	15				
		CT4502	1F-1011A, V0-0.3V, VCC-4.3V			-		
		CT4503						
	CT450	6N135	I <sub>F</sub> =16mA,I <sub>O</sub> =1.1mA,V <sub>CC</sub> =4.5V,	-	0.18	0.4		
		011133	T <sub>A</sub> =25°C					
		6N136	I <sub>F</sub> =16mA, I <sub>O</sub> =3mA, V <sub>CC</sub> =4.5V,	-	0.18 0.4			
		CT4502	T <sub>A</sub> =25°C			0.4		
Vol		CT4503	14-20 0				V	
VOL	Voltage	6N135	I <sub>F</sub> =16mA, I <sub>O</sub> =0.8mA,	_	_	0.5	ľ	
	6N1 CT4	011100	V <sub>CC</sub> =4.5V					
		6N136	I <sub>F</sub> =16mA, I <sub>O</sub> =2.4mA,					
		CT4502	V <sub>CC</sub> =4.5V	-		0.5		
		CT4503	VCC-7.5 V					



# **Electrical Characteristics** $T_A = 0 - 70^{\circ}\text{C}$ (unless otherwise specified). Typical values are measured at $T_A = 25^{\circ}\text{C}$ and $V_{cc} = 5V$

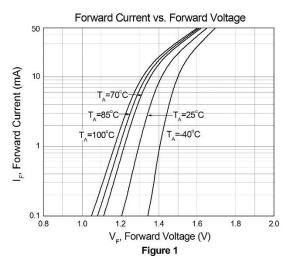
## **Switching Characteristics**

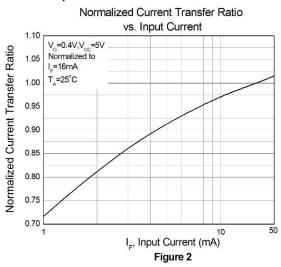
Symbol	Paramete	ers	Test Conditions	Min	Тур	Max	Units	Notes
	Propagation Delay	6N135	R <sub>L</sub> =4.1KΩ, T <sub>A=</sub> 25°C	-	0.35	1.5		
		Time Logic High to	CCIVIO	R <sub>L</sub> =4.1KΩ	-	-	2.0	
$T_PHL$	Logic Low	6N136	R <sub>L</sub> =1.9KΩ, T <sub>A</sub> =25°C	-	0.35	0.8	μs	
	Logic Low	CT4502 CT4503	R <sub>L</sub> =1.9KΩ	-	-	1.0		
	December Delev	CNIAGE	R <sub>L</sub> =4.1KΩ, T <sub>A=</sub> 25°C	-	0.5	1.5		
	Propagation Delay Time Logic Low to	6N135	R <sub>L</sub> =4.1KΩ	-	-	2.0		
$T_PLH$	Logic High	6N136	R <sub>L</sub> =1.9KΩ, T <sub>A</sub> =25°C	-	0.3	0.8	μs	
Logic High	CT4502 CT4503	R <sub>L</sub> =1.9KΩ	-	-	1.0			
	Common Mode Transient Immunity at Logic High	6N125	I <sub>F</sub> = 0mA , V <sub>CM</sub> =10Vp-p,	1,000	4 000			
		6N135 R <sub>L</sub> =4.1KΩ, T <sub>A</sub> =25°C	1,000	_	_			
СМн		6N136	I <sub>F</sub> = 0mA , V <sub>CM</sub> =10Vp-p,	1,000	_	-	V/µs	
CIVIH		CT4502	R <sub>L</sub> =1.9KΩ, T <sub>A</sub> =25°C	1,000				
		CT4503	I <sub>F</sub> = 0mA , V <sub>CM</sub> =1500Vp-p,	15,000 20	20,000			
		014303	R <sub>L</sub> =1.9KΩ, T <sub>A</sub> =25°C	13,000	20,000			
		6N135	I <sub>F</sub> = 16mA , V <sub>CM</sub> =10Vp-p,	1,000 -	_			
	Common Mode	R <sub>L</sub> =4.1KΩ, T <sub>A</sub> =25°C	1,000	_	_			
CML	Transient Immunity at Logic Low	6N136	$I_F = 16\text{mA}$ , $V_{CM}=10\text{Vp-p}$ ,	1,000	_		V/µs	
OIVIL		CT4502	R <sub>L</sub> =1.9KΩ, T <sub>A</sub> =25°C	1,000	_		ν/μο	
		CT4503	I <sub>F</sub> = 16mA , V <sub>CM</sub> =1500Vp-p,	15,000	20,000			
		014000	R <sub>L</sub> =1.9KΩ, T <sub>A</sub> =25°C	13,000				

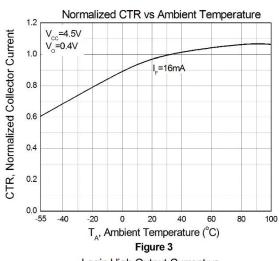


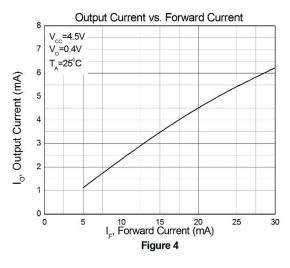
# 1Mbit/s High Speed Phototransistor Optocoupler

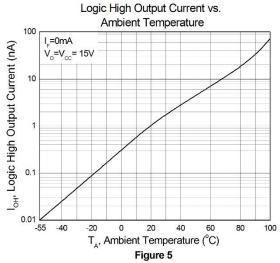
# Typical Characteristic Curves $T_A = 25$ °C, unless otherwise specified

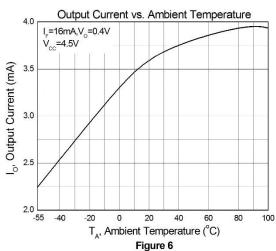








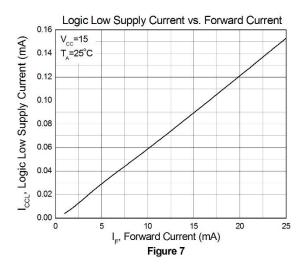


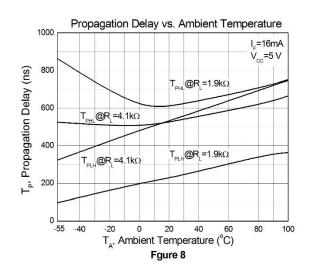


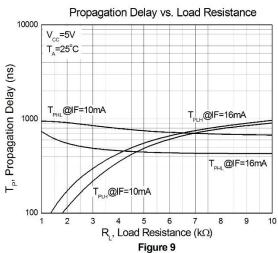


# 1Mbit/s High Speed Phototransistor Optocoupler

# Typical Characteristic Curves $T_A = 25$ °C, unless otherwise specified



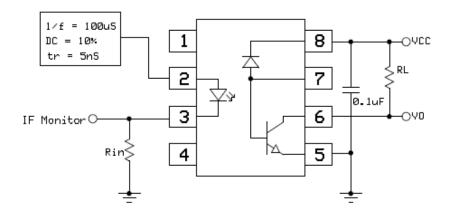


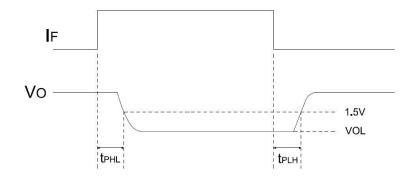




# 1Mbit/s High Speed Phototransistor Optocoupler

## **Test Circuits**





**Figure 10: Switching Time Test Circuits** 



## **Test Circuits**

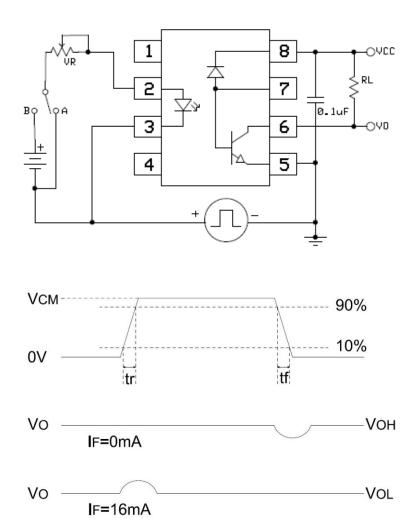
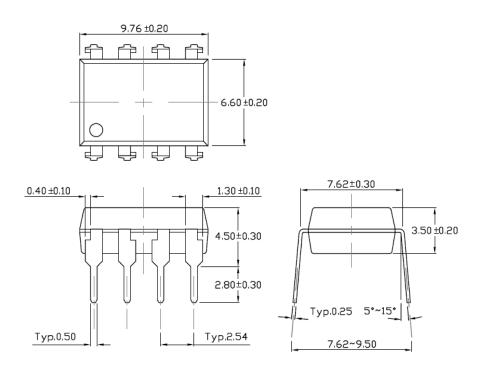


Figure 11: CMR Test Circuit

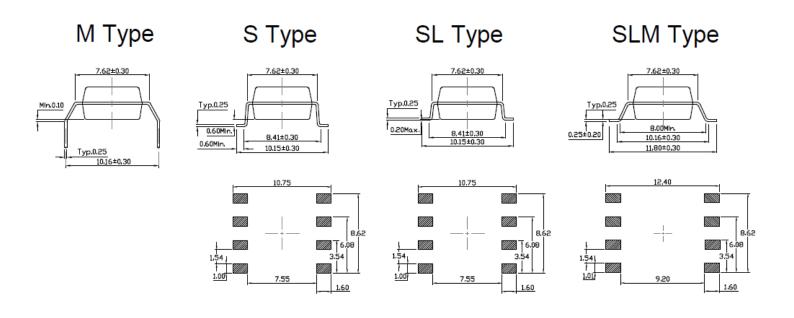


# 1Mbit/s High Speed Phototransistor Optocoupler

# Package Dimension Dimensions in mm unless otherwise stated



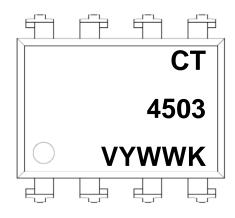
# Package Dimension Dimensions in mm unless otherwise stated





# 1Mbit/s High Speed Phototransistor Optocoupler

# **Marking Information**



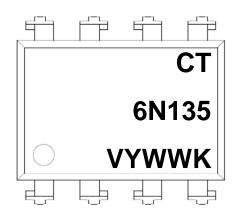
#### Note:

CT : Denotes "CT Micro"

4503 : Part Number

V : VDE Safety Mark Option (Blank or V)

Y : One Digit Year CodeWW : Two Digit Work WeekK : Manufacturing Code



#### Note:

CT : Denotes "CT Micro" 6N135 : Part Number

V : VDE Safety Mark Option (Blank or V)

Y : One Digit Year CodeWW : Two Digit Work WeekK : Manufacturing Code



# 1Mbit/s High Speed Phototransistor Optocoupler

# **Ordering Information**

# 6N13X(V)(Y)(Z)

X = Part Number (5,6 for 6N13X series)

V = VDE Safety Mark Option (Blank or V)

Y = Lead Form Option (S, SL, M, SLM or none)

Z = Tape and Reel Option (Blank, T1 or T2)

# CT450X(V)(Y)(Z)

X = Part Number (2,3 for CT450X series)

V = VDE Safety Mark Option (Blank or V)

Y = Lead Form Option (S, SL, M, SLM or none)

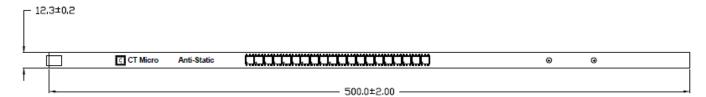
Z = Tape and Reel Option (Blank, T1 or T2)

Option	Description	Quantity
None	Standard 8 Pin Dip	40 Units/Tube
M	Gullwing (400mil) Lead Forming	40 Units/Tube
S(T1)	Surface Mount Lead Forming – With Option 1 Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option 2 Taping	1000 Units/Reel
SL(T1)	Surface Mount (Low Profile) Lead Forming– With Option 1 Taping	1000 Units/Reel
SL(T2)	Surface Mount (Low Profile) Lead Forming– With Option 2 Taping	1000 Units/Reel
SLM(T1)	Surface Mount (Gullwing) Lead Forming–With Option 1 Taping	1000 Units/Reel
SLM(T2)	SLM(T2) Surface Mount (Gullwing) Lead Forming – With Option 2 Taping	

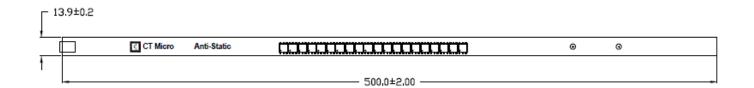


# Carrier Specifications Dimensions in mm unless otherwise stated

#### **Tube Option Standard DIP**



## **Tube Option M Type**

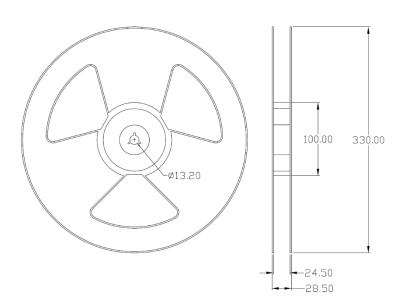


# Reel Dimension All dimensions are in mm, unless otherwise stated

## Option S(T1/T2) & SL(T1/T2)

# 100.00 330.00 \$\delta 13.20 \\ \$\delta 16.50 \\ \$\delta 20.50 \\ \$\delta 20.50

# Option SLM(T1/T2)

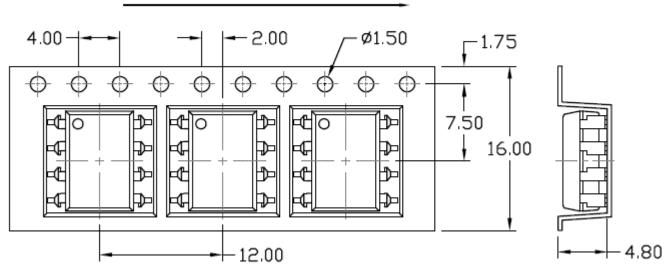




## Carrier Tape Specifications Dimensions in mm unless otherwise stated

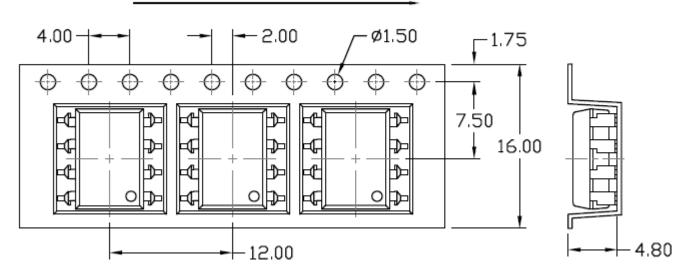
Option S(T1) & SL(T1)

# Input Direction



# Option S(T2) & SL(T2)

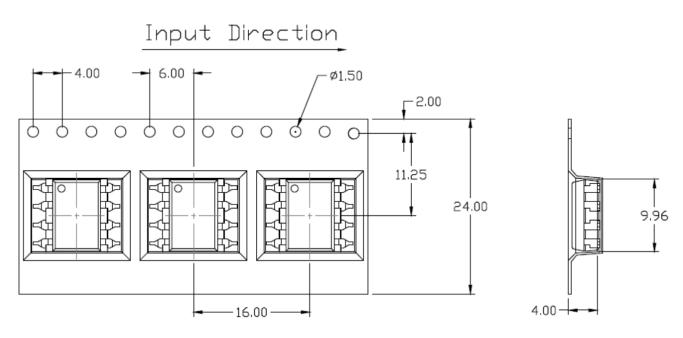
# Input Direction



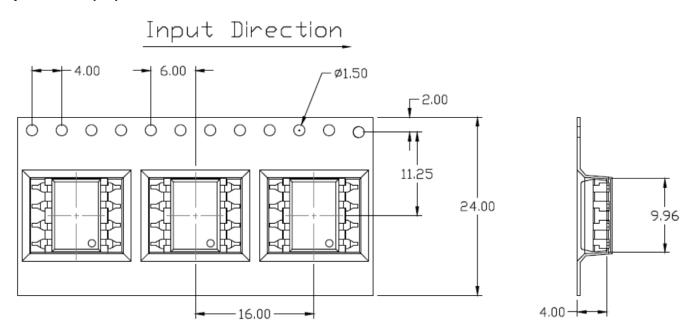


# Carrier Tape Specifications Dimensions in mm unless otherwise stated

# Option SLM(T1)



## **Option SLM(T2)**





# 1Mbit/s High Speed Phototransistor Optocoupler

#### **Solderability spec (Follow the JEDEC standard JESD22-B102)**

Reflow Soldering: Immersed surface, other than the end of pin as cut-surface, must be covered by solder.

Solder-Bath: More than 95% of the electrode must be covered with solder.

# **Wave soldering (Follow the JEDEC standard JESD22-A111)**

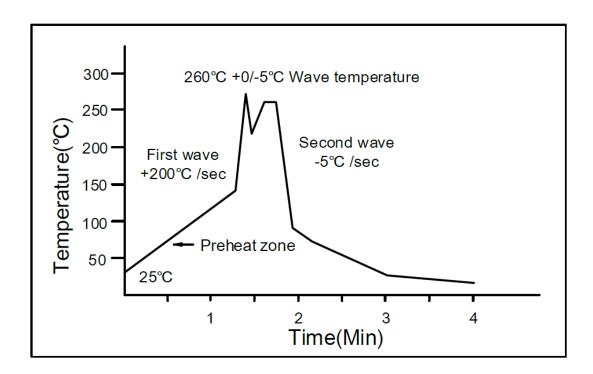
One time soldering is recommended within the condition of temperature.

Temperature: 260+0/-5°C.

Time: 10 sec.

Preheat temperature: 25 to 140°C.

Preheat time: 30 to 80 sec.



# Iron soldering (Follow the standard MIL-STD 202G, Method 210F)

Allow single lead soldering in every single process.

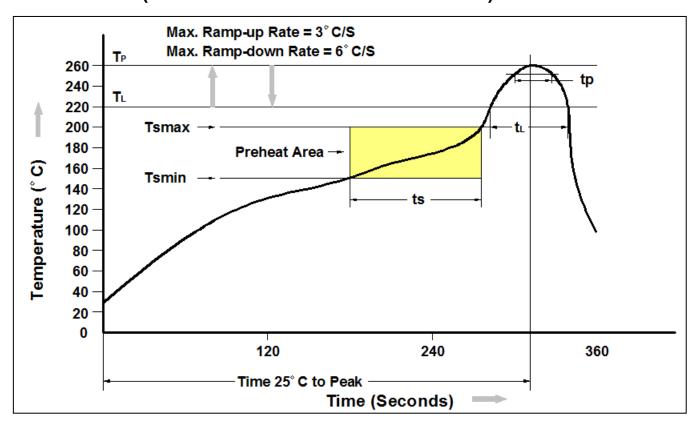
One time soldering is recommended. Temperature: 350±10°C

Time: 5 sec max.



# 1Mbit/s High Speed Phototransistor Optocoupler

# Reflow Profile (Follow the JEDEC standard J-STD-020)



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150°C
Temperature Max. (Tsmax)	200°C
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t∟ to t♭)	3°C/second max.
Liquidous Temperature (T <sub>L</sub> )	217°C
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60 – 150 seconds
Peak Body Package Temperature	260°C +0°C / -5°C
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max
Time 25°C to Peak Temperature	8 minutes max.



#### **DISCLAIMER**

CT MICRO RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. CT MICRO DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS. NOR THE RIGHTS OF OTHERS.

-----

DISCOLORATION MIGHT OCCUR ON THE PACKAGE SURFACE AFTER SOLDERING, REFLOW OR LONG TERM USE. THIS DOES NOT IMPACT THE PRODUCT PERFORMANCE NOR THE PRODUCT RELIABILITY.

CT MICRO ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT EXPRESS WRITTEN APPROVAL OF CT MICRO INTERNATIONAL CORPORATION.

- 1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, or (c) whose failure to perform when properly used in accordance with instruction for use provided in the labelling, can be reasonably expected to result in significant injury to the user.
- A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.